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Supply Center	Ray Monnin	MILITARY DR This drawing is available for	use by		
Dayton, Ohio	CHECKED BY	all Departments and Agencies Department of Defense	of the		
Original date	Du Di ango	TITLE: MICROCIRCUITS, PROG INTERVAL TIMER, MONOLITHIC	RAMMABLE		
of drawing:	APPROVED BY	INTĒRVAL TIMER, MONOLITHIC	SILICON		
22 June 1987	SIZE CODE IDENT. NO.	DWG NO. FOCO OT	2520		
AMSC N/A	A 14933	5962-87			
AMSC NIA	REV	PAGE 1 OF	16		

1. SCOPE

- 1.1 Scope. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices."
 - 1.2 Part number. The complete part number shall be as shown in the following example:

5962-87520	01	J	X
		<u> </u>	
	1	1	1
Drawing number	Device type	Case outline	Lead finish per
-	(1.2.1)	(1.2.2)	MIL-M-38510

1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	8253	Programmable interval timer
02	8253	Programmable interval timer
03	8253-5	Programmable interval timer

1.2.2 <u>Case outline</u>. The case outline shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter

D-3 (24-lead, 1/2" x 1-1/4"), dual-in-line package

1.3 Absolute maximum ratings.

Supply voltage range	-0.5 V dc to +7.0 V dc
Input voltage range with respect to ground (any pin)	-0.5 V dc to +7.0 V dc -65°C to +150°C
Storage temperature range $ -$	-65 C to +150 C
Lead temperature (soldering, 10 seconds)	+270°C
Thermal resistance, junction-to-case (θυς): Case J	See MIL-M-38510, appendix C
Junction temperature (T_J)	+150°C
1.4 Recommended operation conditions.	

Supply voltage (V_{CC}) - - - - - - - - - 5 V dc $\pm 10\%$ for dc testing Supply voltage (V_{CC}):

01 and 03 devices - - - - - - - - - 5 V dc $\pm 10\%$ for ac testing 02 device - - - - - - - - - - - 5 V dc $\pm 5\%$ for ac testing Minimum high-level input voltage (V_{IL}) - - - - - 2.2 V dc Minimum low-level input voltage (V_{IL}) - - - - - - - - - - - - - - 0.5 V dc

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DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO

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2. APPLICABLE DOCUMENTS

2.1 Government specifications and standards. Unless otherwise specified, the following specification and standard, of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510

- Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883

- Test Methods and Procedures for Microelectronics.

(Copies of the specification and standard required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
 - 3.2.1 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.2 Truth tables. The truth tables shall be as specified on figure 2.
 - 3.2.3 Block diagram. The block diagram shall be as specified on figure 3.
 - 3.2.4 Case outline. The case outline shall be in accordance with 1.2.2 herein.
- 3.3 Electrical performance characteristics. Unless otherwise specified, the electrical performance characteristics are as specified in table I and apply over the full recommended case operating temperature range.
- 3.4 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in 6.5 herein.

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		TABLE I. Electrical perform	ance charact	eristics.	·		
Test	Symbol	Conditions -55°C ≤ T _C ≤ +125°C	Group A subgroups	Device types	i	mits	 Unit
	<u>i</u>	unless otherwise specified		 	Min 	Max	<u> </u>
Input low voltage	i v _{IL}	V _{CC} = 5 V ±10%	1, 2, 3 	A11		.7	V
Input high voltage	V _{IH}	V _{CC} = 5 V ±10%	1, 2, 3	 All 	2.2	 	V
Output low voltage	Y _{OL}	V _{CC} = 5 V ±10% I _{OL} = 1.6 mA	1, 2, 3	i All I	 	.45	 V
Output high voltage	V _{ОН}	V _{CC} = 5 V ±10% I OH = -150 μA	1, 2, 3	 A11 	 2.4 	 	V
Input load current	IIL	V _{CC} = 5.5 V V _{IN} = V _{CC} to 0 V	1, 2, 3	 A11 	 	 ±20 	Ι μ Α
Output float leakage	IOFL	V _{CC} = 5.5 V V _{OUT} = V _{CC} to 0 V	1, 2, 3	 A11 	 	 ±20 	Ι μΑ
V _{CC} supply current 1/	1 _{CC}	V _{CC} = 5.5 V Outputs unloaded static	1, 2, 3	A11 		160	l mA l
Input capacitance	CIN	See 4.3.1d F _C = 1 MHz T _A = 25°C; V _{CC} = GND = 0 V	4	 A11 	 	 10 	pF
Input/output capacitance	CI/0	Unmeasured pins returned to V _{SS} C; V _{CC} = GND = 0 V	4 4 	 A11 	 	 20 	 pF
Address stable before RD	t _{AR}	V _{CC} = 5 V ±10% for 01 and 03 devices V _{CC} = 5 V ±5% for 02	9, 10, 11	01,02	 50 	 	ns
		děvice See figures 4 and 5 <u>2</u> /	 	03	30	1 	ns

See footnotes at end of table.

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	TAE	BLE I. Electrical performance	characterist	tics - Cor	tinued.		
Test	Symbol	Conditions	l Group A	Device	! <u>L</u>	imits	Unit
	 	$-55^{\circ}C < T_C < +125^{\circ}C$ unless otherwise specified	subgroups 	types 	l Min 	Max	
Address hold time for RD	t _{RA}	V _{CC} = 5 V ±10% for 01 and 03 devices V _{CC} = 5 V ±5% for 02	9, 10, 11	A11	5 	 	ns
RD pulse width 3/	t _{RR}	l device See figures 4 and 5	9, 10, 11	01,02	400	 	ns
	į	2/	i 1	03	300	i	ns
Data delay from RD 4/	t _{RD}	_ 	9, 10, 11	01,02		1 300 1	ns
_		 	 	03		200	ns
RD to data floating	t _{DF}	 	9, 10, 11	01,02	25	125	ns
<u>5</u> /	 		 	03	25 	100	ns
Recovery time between RD 5/ and any other control signal	t _{RV}	 	9, 10, 11	A11 	1	1	μs
Address stable before WR	t _{AW}	!	9, 10, 11	01,02	50		ns
	 			03	30		ns
Address hold time for WR	t _{WA}		9, 10, 11	A11 A11 	30		ns
WR pulse width	t _{WW}		9, 10, 11	01,02	400		l ns
<u>3</u> /	İ			i	300	T	l ns

See footnotes at end of table.

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03

i 300

ns

	TAB	LE I. Electrical performance	characterist	<u>ics</u> - Con	tinued.		
Test	 Symbol	Conditions -55°C ≤ T _C ≤ +125°C	Group A	Device	L	imits	Unit
	 	-55°C < T _C < +125°C unless otherwise specified 	subgroups 	types 	l Min 	 Max 	
Data setup time for WR	t _{DW}	 V _{CC} = 5 V ±10% for 01 and 03 devices	9, 10, 11	01,02	300		ns
	 	V_{CC} = 5 V ±5% for 02 device See figures 4 and 5 2/		03	250		ns
Data hold time for WR	t _{WD}		9, 10, 11	01,02	40		ns
	 	1		03 	 30 	1	ns
Recovery time between WR 5/ and any other control signal	t _{RV}		9, 10, 11	 All 	1 1 		μS
Clock period	t _{CLK}		9, 10, 11	A11	i 380	5/ DC	ns
High pulse width	tpWH		9, 10, 11	A11	230 		ns
Low pulse width	tpWL		9, 10, 11	A17	150		ns
Gate width high	t _{GW}	 	9, 10, 11	 A11 	150		ns
Gate width 1 ow 5/	t _{GL}	i - -	9, 10, 11	A11	100		ns
Gate setup to CLK high	t _{GS}	 	9, 10, 11	 A11 	100 	1	ns
Gate hold after CLK high	t _{GH}	` -	9, 10, 11	A11	i 55		ns

See footnotes at end of table.

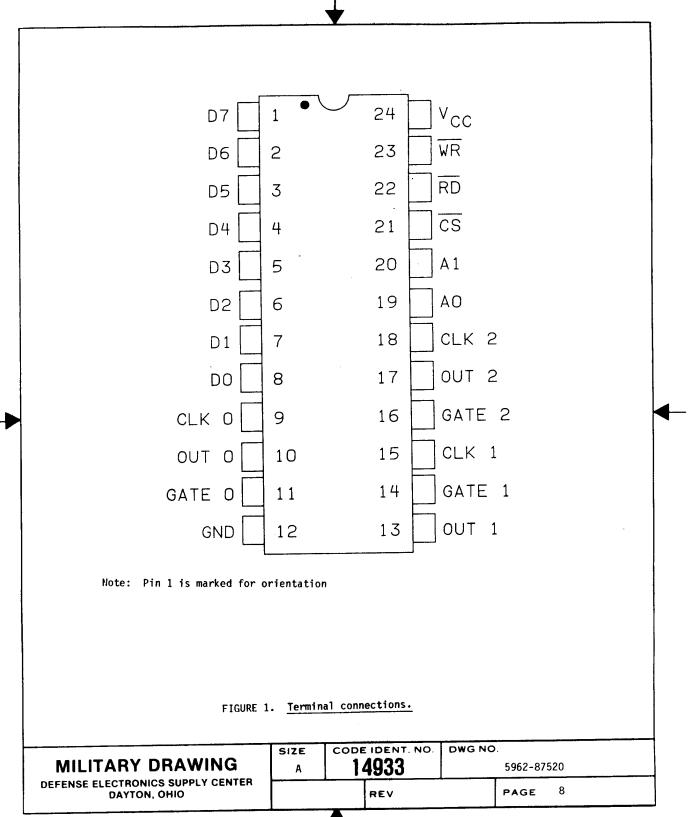
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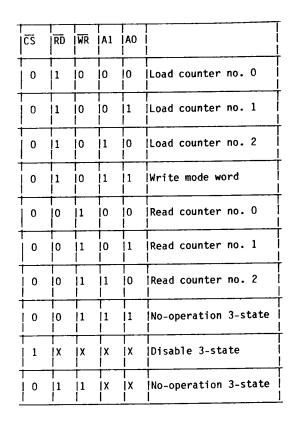
TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions -55°C < T _C < +125°C	Group A	Device	<u> L</u>	imits	Unit
	1	-55 C < IC < +125 C unless otherwise specified 	l subgroups i	l types l	i Min	Max	
4/ Output delay from CLK low	t ₀₀	V _{CC} = 5 V ±10% for 01 and 03 devices V _{CC} = 5 V ±5% for 02	9, 10, 11	A11 	 	400	ns
4/ Output delay from gate low	topg	device See figures 4 and 5 <u>2</u> /	9, 10, 11	 A11 	 	1 300 1	ns

- 1/ I_{CC} is measured in a static condition with no output loads applied.
- $\underline{2}/$ Test conditions: V_{IL} = 0.45 V $_{IH}$ = 2.4 V $_{0L}$ = 0.8 V $_{0H}$ = 2.2 V
- 3/ If clock low occurs less than 100 ns after the rising edge of READ or WRITE, the counter selected during the READ or WRITE could be affected.
- 4/ Test condition: $C_L = 100 \text{ pF}$.
- 5/ Guaranteed, if not tested.
- 3.5 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in 6.5. The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall state that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.6 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.7 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.8 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).

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Control word format

D5 D4 D3 D2 D1 D0 D6

T		1				l	1	ļ
SC1	ISC0	RL1	RLO	M2	M1	MO	BCD	ļ
1	1	1	1	1	<u> 1</u>	<u> </u>	1	<u> </u>

Definition of control

SC - Select counter:

SC1 SC0

0	10	
0	1 1	
1	1 0 	Select counter 2
1	1	

RL1 RLO

	1	
0) 0 	Counter latching operation
1	0	
0	1	
1	1 1	

Mode register for latching count AO, A1 = 11

D6 D5 D4 D3 D2 D1 D0

1	T		T			_	<u> </u>	Т
SC1	isco	ĺΟ	10	ĺΧ	ΙX	ΙX	ĮΧ	ļ
	1			<u> </u>	<u> </u>	<u> </u>	_ <u> </u>	

- Specify counter to be latched. SC1, SCO

- 00 designates counter latching operation.

- Don't care

FIGURE 2. Truth tables.

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D5, D4

Gate pin operations summary

	Sig	Signal status					
Modes	Low or going low	 Rising	High				
0	 Disables counting	-	Enables counting				
1	-	1) Initiates counting 2) Resets output after next clock	-				
2	1) Disables counting 2) Sets output immediately high	, _ ,	Enables counting 				
3	Disables counting	 Initiates counting 	Enables counting				
4	 Disables counting	! - 	 Enables counting 				
5	-	 Initiates counting	- I				

M- Mode: M2

1

0 |1

|Mode 0 10 10 10 Mode 1 10 10

Mode 2

M1 M0

Mode 3 IX 1 11 |Mode 4 1 10 10 Mode 5

0

BCD:

10	 Binary counter 16-bits 	_

FIGURE 2. Truth tables - Continued.

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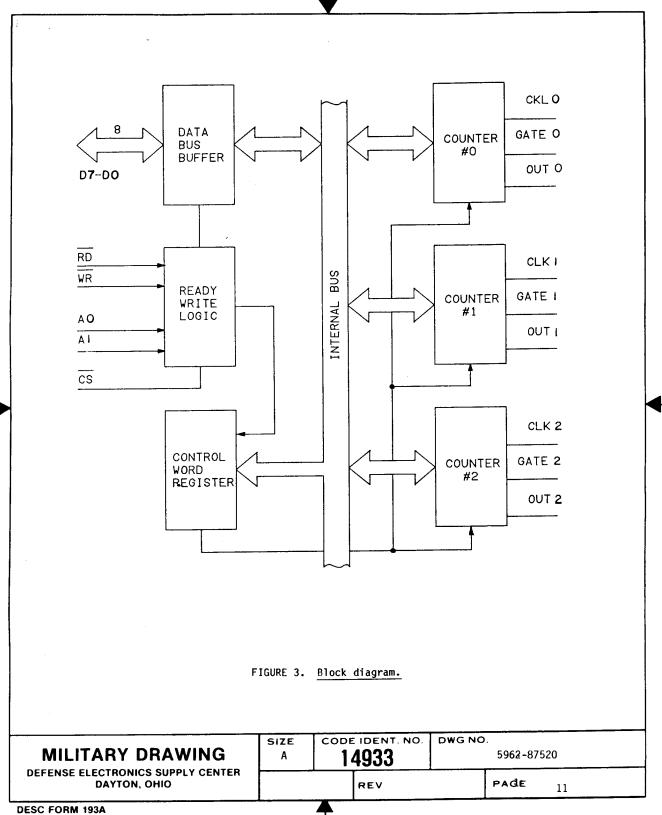
DWG NO.

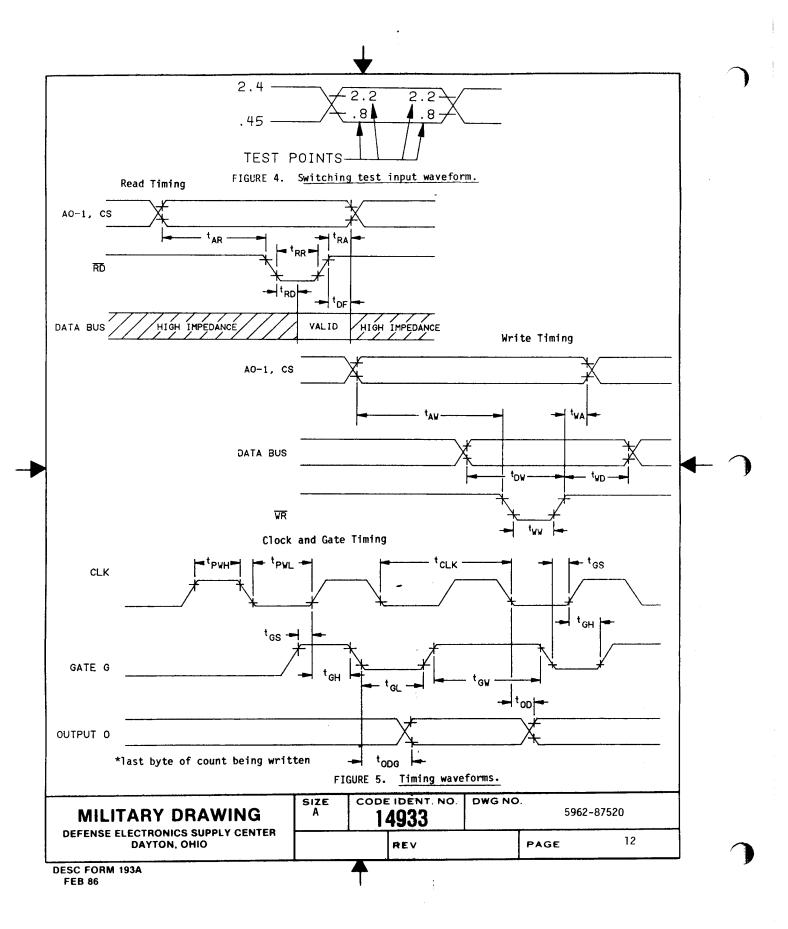
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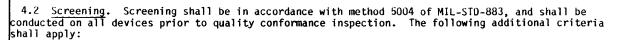
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- a. Burn-in test (method 1015 of MIL-STD-883).
 - (1) Test condition D using the circuit submitted with with the certificate of compliance (see 3.5 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method $\overline{5005}$ of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
 - 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - c. Subgroups 7 and 8 are verified by testing to the truth tables of figure 2.
 - d. Subgroup 4 (C $_{\rm IN}$ and C $_{\rm I/O}$ measurements) shall be measured initially and after process or design changes which may affect capacitance.
 - 4.3.2 Groups C and D inspections.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. Steady-state life test (method 1005 of MIL-STD-883) conditions:
 - (1) Test condition D using the circuit submitted with the certificate of compliance (see 3.5 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by appendix B of MIL-M-38510 and method 1005 of MIL-STD-883.

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Initial electrical parameters (method 5004)	+
Final electrical test parameters (method 5004)	1*, 2, 3, 7, 8, 9, 10, and 11
Group A test requirements (method 5005)	1*, 2, 3, 7, 8, 9, 10, and 11
Groups C and D end-point electrical parameters (method 5005)	1, 2, 3 or 2, 8(hot), and 10
Additional electrical subgroups for group C periodic inspections	

- * PDA applies to subgroup 1.
- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- 6. NOTES
- 6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

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6.3 Pin description.

Pin number	l Name	1/0	Description
1-8	D7-D0	1/0	Data bus (8-bit)
9, 15, 18	CLK N	l I	Counter clock inputs
11, 14, 16	GATE N	I	Counter gate inputs
10, 13, 17	OUT N	0	Counter outputs
22	RD	I	Read counter
23	WR .	I	Write command or data
21	cs	I	Chip select
19, 20	A0-A1	I	Counter select
24	V _{CC}		+5 volts
12	GND		Ground

6.4 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5375.

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6.5 Approved source of supply. Approved sources of supply are listed herein. Additional sources will be added as they become available. The vendors listed herein have agreed to this drawing and a certificate of compliance (see 3.5 herein) has been submitted to DESC-ECS.

Military drawing part number	Vendor CAGE number	Vendor similar part number $1/$	Replacement military specification part number
5962-8752001JX	34335	8253/BJA	
5962-8752002JX	34649	MD8253/B	
5962-8752003JX	34335	8253-5/BJA	

 $\frac{1}{2}$ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address	
34335	Advanced Micro Devices, Inc. 901 Thompson Place P.O. Box 3453 Sunnyvale, CA 94088	
34649	Intel Corporation 5000 W Williams Field Road Chandler A7 85224	

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